

NPN Power Silicon Transistor



Rev. V4

Features

- Available in JAN, JANTX, JANTXV per MIL-PRF-19500/407
- TO-3 (TO-204AA) Package
- Designed for General Purpose Switching and Amplifier Applications



Electrical Characteristics (T_A = +25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Units	Min.	Max.		
Off Characteristics							
Collector - Emitter Breakdown Voltage	I_{C} = 200 mA dc I_{C} = 200 mA dc, R _{BE} = 100 Ω V _{BE} = -1.5 V dc, I _C = 200 mA dc	V _{(BR)CEO} V _{(BR)CER} V _{(BR)CEX}	V dc	70 80 90	_		
Collector - Emitter Cutoff Current	V_{CE} = 60 Vdc V_{BE} = -1.5 V dc, V_{CE} = 100 V dc	I _{CEO} I _{CEX1}	mA dc	_	1 1		
Emitter - Base Cutoff Current	V _{EB} = 7.0 V dc	I _{EBO}	mA dc	—	1		
On Characteristics							
Forward Current Transfer Ratio	$ I_C = 0.5 \text{ A dc}, V_{CE} = 4.0 \text{ V dc} I_C = 4.0 \text{ A dc}, V_{CE} = 4.0 \text{ V dc} I_C = 10.0 \text{ A dc}, V_{CE} = 4.0 \text{ V dc} $	h _{FE}	-	40 20 5	60 —		
Collector - Emitter Saturation Voltage	I_{C} = 4.0 A dc, I_{B} = 0.4 A dc I_{C} = 10.0 A dc, I_{B} = 3.3 A dc	V _{CE(SAT)}	V dc	—	0.75 2.0		
Emitter - Base Saturation Voltage	I_{C} = 4.0 A dc, V_{CE} = 4.0 V dc	$V_{BE(SAT)}$	V dc	_	1.4		
Dynamic Characteristics							
Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio	I _C = 1 A dc, V _{CE} = 4.0 Vdc, f = 100 kHz	h _{fe}		8	40		
Output Capacitance	V_{CB} = 10 Vdc, I _E = 0, 100 kHz ≤ f ≤ 1 MHz	C _{obo}	pF	_	700		
Switching Characteristics							
Turn-On Time	V_{CC} = 30 Vdc; I _C = 4.0 A dc; I _B 1 = 0.4 A dc	t _{on}	μs	_	6		
Turn-Off Time	$I_{\rm C}$ = 4.0 A dc; $I_{\rm B}$ 1= - $I_{\rm B}$ 2= 0.4 A dc	t _{off}	μs	_	12		
Safe Operating Area							
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	5 A dc						

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Parameter	Test Conditions	Symbol	Units	Min.	Max.
Base Emitter Voltage (unsaturated)	V_{CE} = 4 V dc, I _C = 4 A dc	V_{BE}	V dc		1.4
Collector - Emitter Cutoff Current	$T_A = +150^{\circ}C$ $V_{CE} = 100 Vdc$ $V_{BE} = -1.5 V dc$	I _{CEX2}	mA dc	_	10
Forward - Current Transfer Ratio	$T_{A} = -55^{\circ}C$ $V_{CE} = 4 V dc, I_{C} = 4 A dc$	h _{FE4}		15	
Collector—Emitter Saturated Voltage	I _C = 10 A dc, I _B = 3.3 A dc	V _{CE(sat)2}	V dc		2

Absolute Maximum Ratings ($T_A = +25^{\circ}C$ unless otherwise noted)

Ratings	Symbol	Value
Collector - Emitter Voltage	V_{CEO}	70 V dc
Collector - Base Voltage	V_{CBO}	100 V dc
Emitter - Base Voltage	V_{EBO}	7 V dc
Base Current	Ι _Β	7 V dc
Collector Current	Ι _C	15 A dc
Total Power Dissipation @ T_A = +25°C ^{1, 2}	Ρ _T	6 W
Total Power Dissipation @ T_c = +25°C ³	PT	117 W
Operating & Storage Temperature Range	T_J, T_{STG}	-65°C to +200°C

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case ⁴		1.5°C/W

1. T_A = room ambient as defined in the general requirements of 4.5 of MIL-STD-750

2. Derate linearly @ 34.2 mW / °C for $T_A = 25$ °C

3. See figure 2 of MIL-PRF-19500/407 for temperature-power derating curves.

4. See figure 3 for transient thermal impedance graph.

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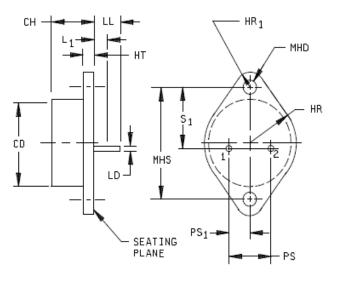
2N3055

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Outline Drawing (TO-3)

	Dimensions				
Symbol	Inches		Millimeters		Notes
	Min	Max	Min	Max	
CD		.875		22.22	
CH	.270	.380	6.86	9.65	
HT	.060	.135	1.52	3.43	
HR	.495	.525	12.57	13.3	
HR ₁	.131	.188	3.33	4.78	
LD	.038	.043	0.97	1.09	3
LL	.312	.500	7.92	12.70	
L ₁		.050		1.27	
MHD	.151	.165	3.84	4.19	
MHS	1.177	1.197	29.90	30.40	
PS	.420	.440	10.67	11.18	4
PS ₁	.205	.225	.521	5.72	4
S1	.655	.675	16.64	17.15	



NOTES:

- 1. Dimensions are in inches. Millimeters are given for general information only.
- 2. Terminal 1, emitter, terminal 2, base, case, collector.
- 3. LD applies between L1 and LL. Diameter is uncontrolled in L1.
- 4. These dimensions should be measured at points .050 to .055 inch (1.27-1.40 mm) below seating plane. When gauge is not used, measurement will be made at the seating plane.
- The seating plane of the header shall be flat within .004 inch (0.10 mm) concave to .004 inch (0.10 mm) convex inside a .930 inch (23.62 mm) diameter circle on the center of the header and flat within .006 inch (0.15 mm) concave to .006 inch (0.15 mm) convex overall.
- Collector shall be electrically connected to the case.
- 7. In accordance with ASME Y14.5M, diameters are equivalent to \$\phix\$ symbology.

FIGURE 1. Physical dimensions of transistor types 2N3055 (similar to TO-204AA).

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